



THE DATASHEET OF ZTX955STZ



ZTX955

PNP SILICON PLANAR ME HIGH CURRENT TRANSIS

ISSUE 3 – JUNE 94

FEATURES

- * 3 Amps continuous current
- * Up to 10 Amps peak current
- * Very low saturation voltage
- * Excellent gain characteristics up to 100MHz
- * Spice model available

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Base-Emitter Turn-On Voltage	V _{BE(on)}		-790	-900	mV	I _C =-3A, V _{CE} =-5V*
Static Forward Current Transfer Ratio	h _{FE}	100	200	300		I _C =-10mA, V _{CE} =-5V*
		100	200			I _C =-1A, V _{CE} =-5V*
		75	140			I _C =-3A, V _{CE} =-5V*
		10	10			I _C =-10A, V _{CE} =-5V*
Transition Frequency	f _T		110		MHz	I _C =-100mA, V _{CE} =-10V f _s =50MHz
Output Capacitance	C _{obo}		40		pF	V _{CE} =-20V, f=1MHz
Switching Times	t _{on} t _{off}		68		ns	I _C =-1A, I _B =-100mA
			1030		ns	I _B =-100mA, V _{CE} =-50V

*Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤2%

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	UNIT
Collector-Base Voltage	V _{CB}	V
Collector-Emitter Voltage	V _{CE}	V
Emitter-Base Voltage	V _{EB}	V
Peak Pulse Current	I _{CP}	A
Continuous Collector Current	I _C	A
Practical Power Dissipation*	P _D	W
Power Dissipation at T _{amb} =25°C	P _{D25}	W
Operating and Storage Temperature Range	T _{STG}	°C

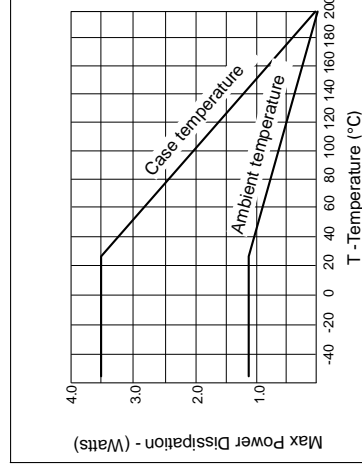
*The power which can be dissipated as a function of ambient temperature. P.C.B. with copper equal to 1 inch square.

ELECTRICAL CHARACTERISTICS

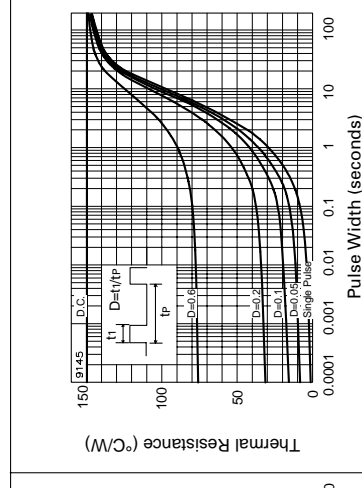
PARAMETER	SYMBOL	UNIT
Collector-Base Breakdown Voltage	V _{(BR)CBO}	V
Collector-Emitter Breakdown Voltage	V _{(BR)CER}	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	V
Collector Cut-Off Current	I _{CBO}	µA
Collector Cut-Off Current	I _{CER}	µA
Emitter Cut-Off Current	I _{EBO}	µA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	V

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient Junction to Case	R _{th(j-amb)}	150	°C/W
	R _{th(j-case)}	50	°C/W



Derating curve



Maximum transient thermal impedance

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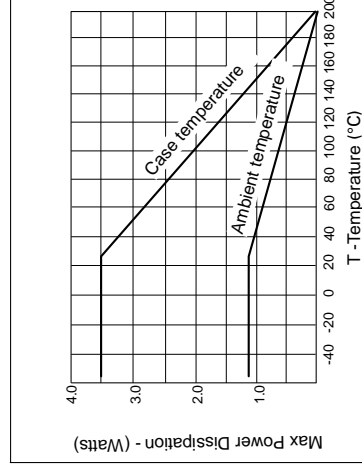
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ELECTRICAL CHARACTERISTICS

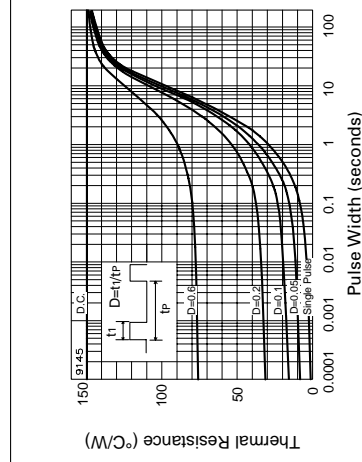
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Base-Emitter Saturation Voltage	V _{BE(sat)}	V

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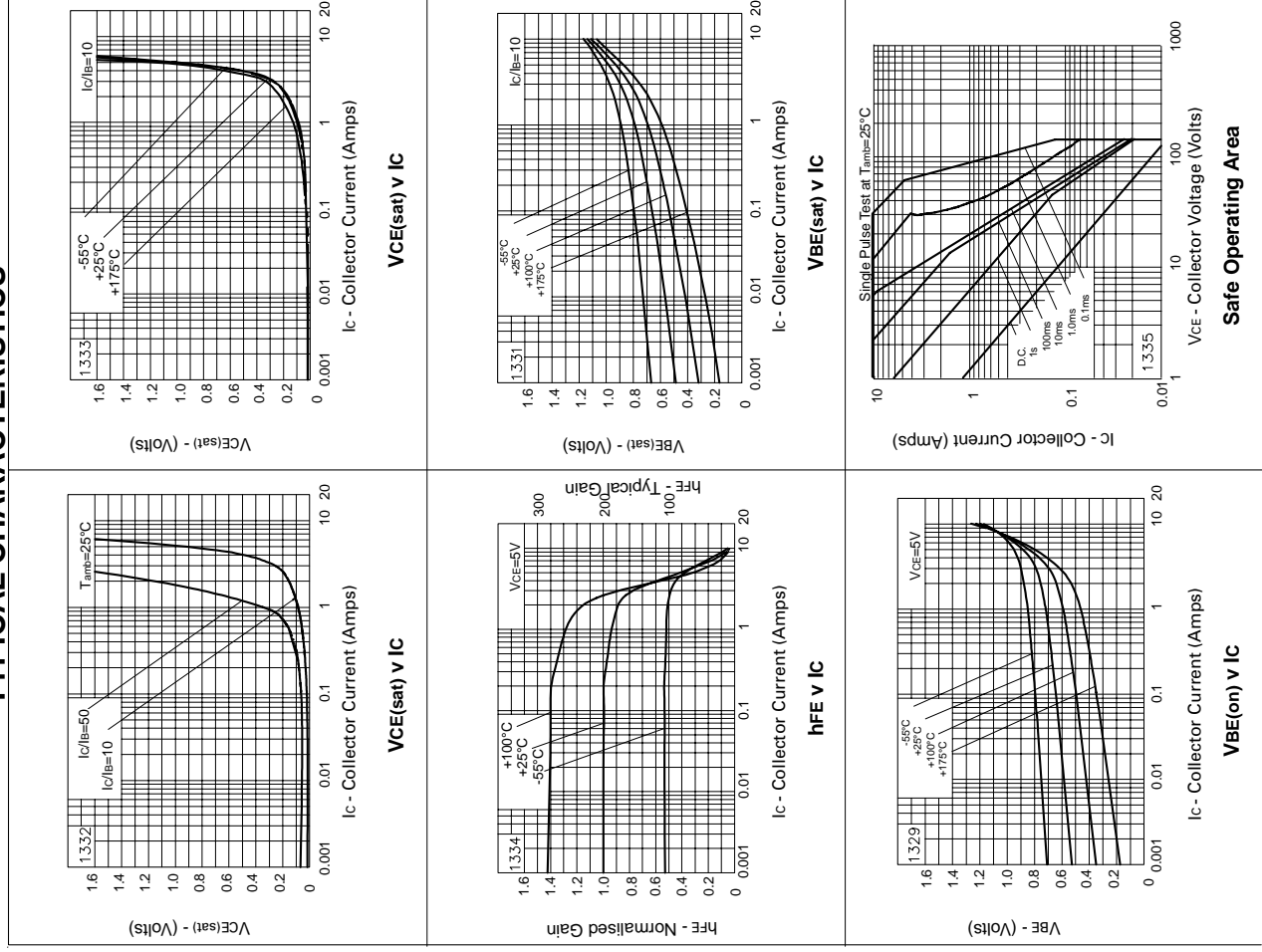
Derating curve



Maximum transient thermal impedance



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TYPICAL CHARACTERISTICS



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